

## RJK0390DPA

# Silicon N Channel Power MOS FET Power Switching

REJ03G1823-0120 Rev.1.20 Sep 29, 2009

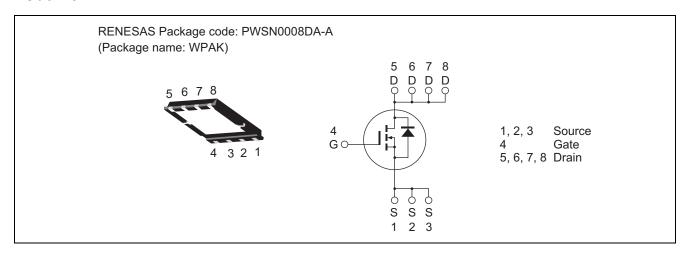
#### **Features**

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} \! = 1.7$  mW typ. (at  $V_{GS} \! = 10$  V)

- Pb-free
- Halogen-free

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

			(1a 25 C)
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	65	A
Drain peak current	I <sub>D(pulse)</sub> Note1	260	A
Body-drain diode reverse drain current	I <sub>DR</sub>	65	A
Avalanche current	I <sub>AP</sub> Note 2	30	A
Avalanche energy	E <sub>AR</sub> Note 2	90	mJ
Channel dissipation	Pch Note3	60	W
Channel to case thermal impedance	θch-c Note3	2.08	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. Tc = 25°C

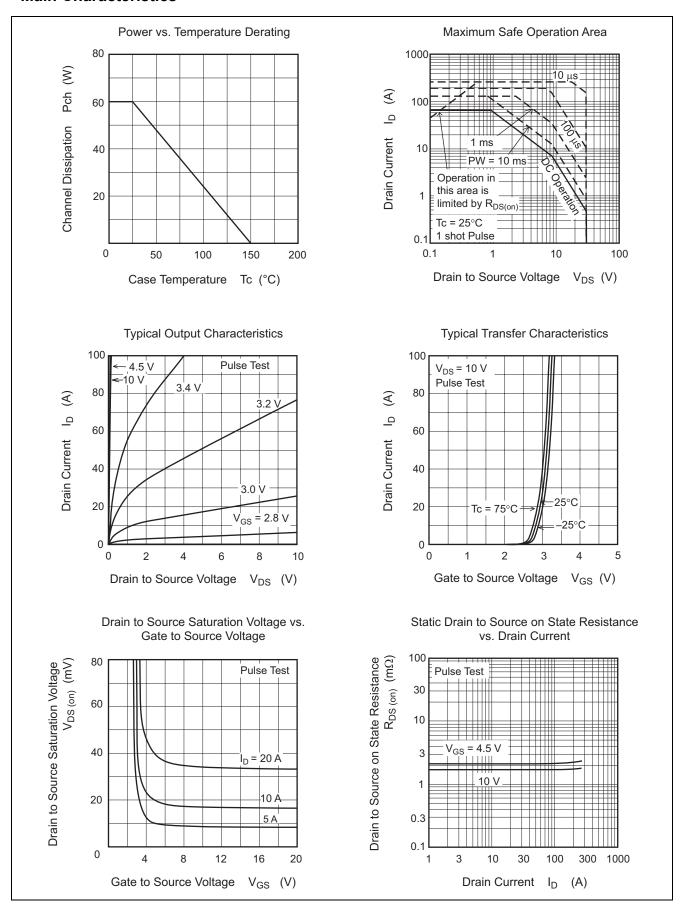
### **Electrical Characteristics**

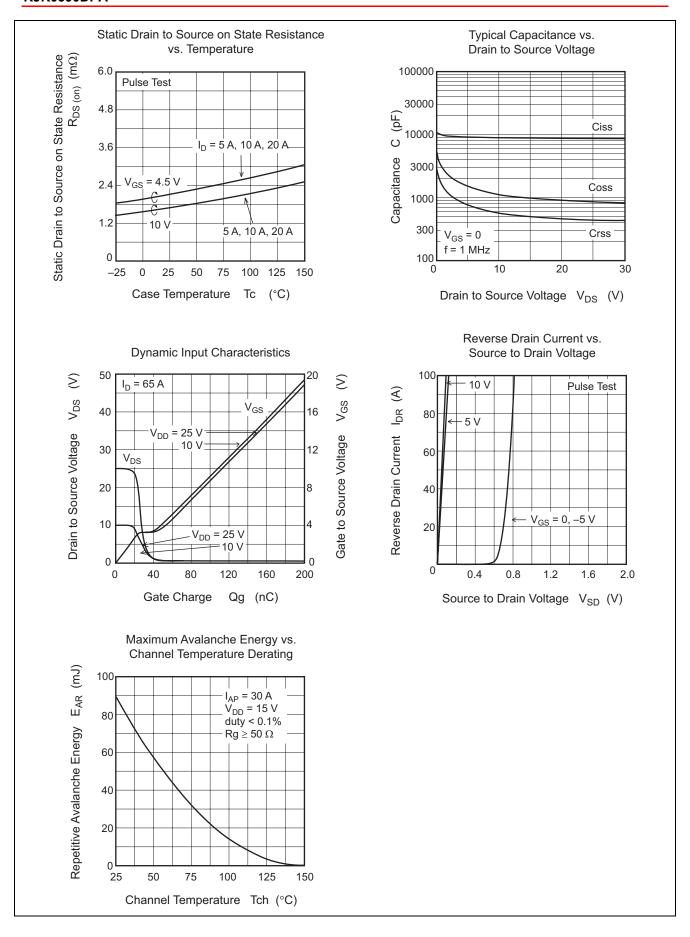
 $(Ta = 25^{\circ}C)$ 

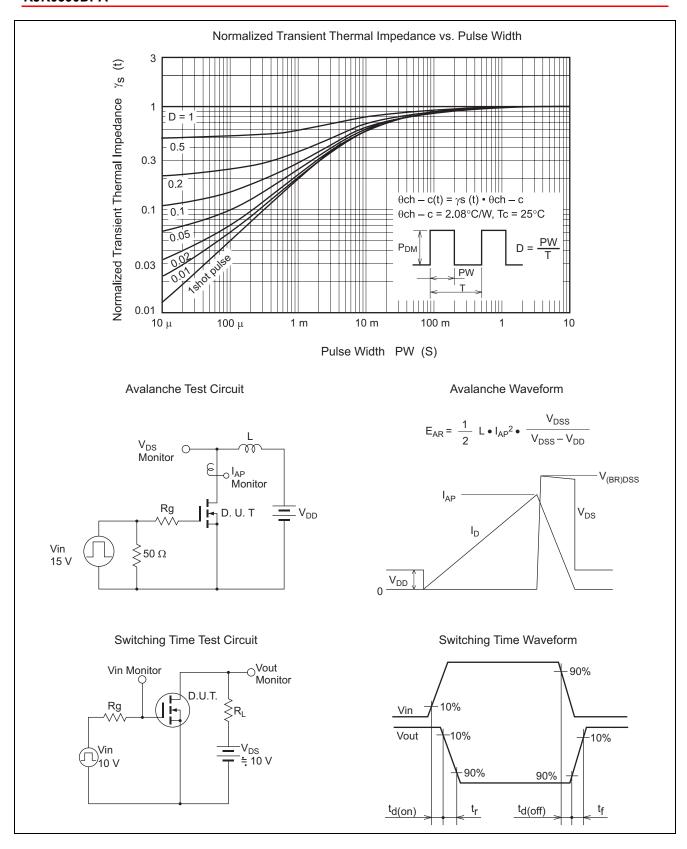
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	_	_	± 0.5	μА	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	l	_	1	μА	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	1.7	2.2	mΩ	$I_D = 32.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R <sub>DS(on)</sub>	_	2.1	2.9	mΩ	$I_D = 32.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y <sub>fs</sub>	_	200	_	S	$I_D = 32.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	8900	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	1120	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	570	_	pF	f = 1 MHz
Gate Resistance	Rg	_	0.80	_	Ω	
Total gate charge	Qg	_	54	_	nC	V <sub>DD</sub> = 10 V
Gate to source charge	Qgs	_	25	_	nC	V <sub>GS</sub> = 4.5 V
Gate to drain charge	Qgd	_	11.3	_	nC	I <sub>D</sub> = 65 A
Turn-on delay time	t <sub>d(on)</sub>	_	22	_	ns	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 32.5 A
Rise time	t <sub>r</sub>	_	10.8	_	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	_	92	_	ns	$R_L = 0.31 \Omega$
Fall time	t <sub>f</sub>	_	37	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	$V_{DF}$	_	0.79	1.03	V	$I_F = 65 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body–drain diode reverse recovery	t <sub>rr</sub>	_	45	_	ns	I <sub>F</sub> =65 A, V <sub>GS</sub> = 0
time						$di_F/dt = 100 A/ \mu s$

Notes: 4. Pulse test

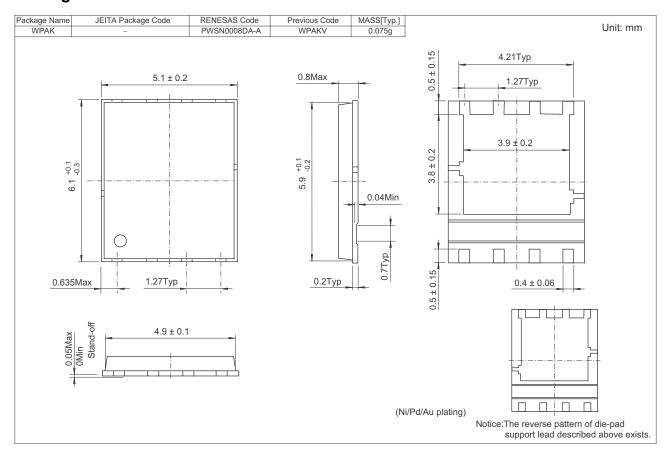
#### **Main Characteristics**







### **Package Dimensions**



### **Ordering Information**

Part No.	Quantity	Shipping Container
RJK0390DPA-00-J53	3000 pcs	Taping

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